



Ultra-High Performance RF Narrowband Transceiver

Applications

- Social Alarms
- Narrowband ultra low power wireless systems with channel spacing down to 4 kHz
- 170 / 315 / 433 / 868 / 915 / 920 / 950 MHz ISM/SRD band systems
- Wireless Metering and Wireless Smart Grid (AMR and AMI)
- IEEE 802.15.4g systems
- Home and building automation
- Wireless alarm and security systems
- Industrial monitoring and control
- Wireless healthcare applications
- Wireless sensor networks and Active RFID
- Private mobile radio

Regulations

Suitable for systems targeting compliance with:

Europe	ETSI EN 300 220 cat. 1 ETSI EN 54-25
	ETSI EN 300 113 and EN 301 166
US	FCC CFR47 Part 15, 24, 90, 101
Japan	ARIB RCR STD-T30, T-67, T-108

Key Features

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- High performance single chip transceiver
 - Adjacent channel selectivity: 67 dB at 6.25 kHz offset
 - Blocking performance: 104 dB at 10 MHz offset
 - Excellent receiver sensitivity:
 - -129 dBm at 300 bps
 - -123 dBm at 1.2 kbps
 - -110 dBm at 50 kbps
 - Very low phase noise: -115 dBc/Hz at 10 kHz offset
- Suitable for systems targeting ETSI category 1
- High spectral efficiency (9.6 kbps in 12.5 kHz channel in compliance with FCC narrowbanding mandate)

Description

The **CC1125** is a fully integrated single-chip radio transceiver designed for high performance at very low power and low voltage operation in cost effective wireless systems. All filters are integrated, removing the need for costly external SAW and IF filters. The device is mainly intended for the ISM (Industrial, Scientific and Medical) and SRD (Short Range Device) frequency bands at 164-192 MHz, 274-320 MHz, 410-480 MHz and 820-960 MHz.

The **CC1125** provides extensive hardware support for packet handling, data buffering, burst transmissions, clear channel assessment, link quality indication and Wake-On-Radio. The **CC1125** main operating parameters can be controlled via an SPI interface. In a typical system, the **CC1125** will be used together with a microcontroller and only few external passive components.

- Power Supply
 - Wide supply voltage range (2.0 V 3.6 V)
 - Low current consumption:
 - RX: 2 mA in RX Sniff Mode
 - RX: 17 mA peak current in low power mode
 - RX: 26 mA peak current in high
 - performance mode
 - TX: 47 mA at +14 dBm
 - Power down: 0.3 μA
- Programmable output power up to +16 dBm with 0.4 dB step size
- Automatic output power ramping
- Configurable data rates: 0 to 200 kbps
- Supported modulation formats: 2-FSK, 2-GFSK, 4-FSK, 4-GFSK, MSK, OOK
- WaveMatch: Advanced digital signal processing for improved sync detect performance
- RoHS compliant 5x5mm QFN 32 package

Peripherals and Support Functions

- Enhanced Wake-On-Radio functionality for automatic low-power receive polling
- Separate 128-byte RX and TX FIFOs
- Includes functions for antenna diversity support
- Support for re-transmissions
- Support for auto-acknowledge of received packets
- TCXO support and control, also in power modes
- Automatic Clear Channel Assessment (CCA) for listenbefore-talk (LBT) systems
- Built in coding gain support for increased range and robustness
- Digital RSSI measurement
- Support for seamless integration with the **CC1190** for increased range giving up to 3 dB improvement in sensitivity and up to +27 dBm output power
- Temperature sensor

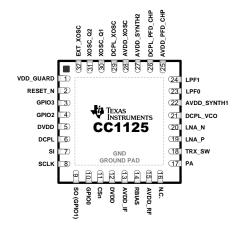




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CC1125

1 Electrical Specifications

All measurements performed on CC1120EM_868_915 rev.1.0.1, CC1120EM_955 rev.1.2.1, CC1120EM_420_470 rev.1.0.1 or CC1120EM_169 rev.1.2 ($f_{xosc} = 32$ MHz), and CC1125EM_868_915 rev.1.1.0, CC1125EM_420_470 rev.1.1.0, CC1125EM_169 rev.1.1.0, CC1125EM-Cat1-868 ($f_{xosc} = 40$ MHz)

1.1 Absolute Max Ratings

Parameter	Min	Тур	Max	Unit	Condition
Supply Voltage ("VDD")	-0.3		3.9	V	
Storage Temperature Range	-40		125	°C	
Solder Reflow Temperature			260	°C	According to IPC/JEDEC J-STD- 020
ESD			2000	V	НВМ
ESD			500	V	CDM
Moisture Sensitivity Level			MSL3		
Input RF level			+10	dBm	
Voltage on Any Digital Pin	-0.3		VDD+0.3 max 3.9	V	
Voltage on Analog Pins (including "DCPL" pins)	-0.3		2.0	V	

1.2 General Characteristics

Parameter	Min	Тур	Max	Unit	Condition
Voltage Supply Range	2.0		3.6	V	
Temperature Range	-40		85	°C	

1.3 **RF Characteristics**

Parameter	Min	Тур	Max	Unit	Condition
	820		960	MHz	
	410		480	MHz	
Frequency Bands	274		320	MHz	Please see application note SWRA398 for more information
	164		192	MHz	
		30		Hz	In 820-960 MHz band
Frequency Resolution		15		Hz	In 410-480 MHz band
		6		Hz	In 164-192 MHz band
Datarate	0		200	kbps	Packet mode
	0		100	kbps	Transparent mode
Datarate Step Size		1e-4		bps	



1.4 Regulatory Standards

Performance Mode	Frequency Band	Suitable for compliance with	Comments		
		ARIB T-108			
		ARIB T-96			
		ETSI EN 300 220 category 1			
		ETSI EN 54-25	Performance also suitable for systems		
	820 – 960 MHz	FCC PART 101	targeting maximum allowed output		
	020 - 900 Wi 12	FCC PART 24 SUBMASK D	power in the respective bands, using a range extender such as the CC1190		
		FCC PART 15.247			
		FCC PART 15.249			
		FCC PART 90 MASK G			
		FCC PART 90 MASK J			
		ARIB T-67			
High Performance		ARIB RCR STD-30			
Mode	410 – 480 MHz	ETSI EN 301 166	Performance also suitable for systems targeting maximum allowed output power in the respective bands, using a range extender		
		ETSI EN 300 113			
		ETSI EN 300 220 category 1			
		FCC PART 90 MASK D			
		FCC PART 90 MASK E			
		FCC PART 90 MASK G			
		ETSI EN 300 220 category 1			
		ETSI EN 301 166	Derformence also quitable for quaterna		
	164 – 192 MHz	ETSI EN 300 113	Performance also suitable for systems targeting maximum allowed output		
	104 - 132 10112	FCC PART 90 MASK C	power in the respective bands, using a range extender		
		FCC PART 90 MASK D			
		FCC PART 90 MASK E			
		ETSI EN 300 220 category 2			
	820 – 960 MHz	FCC PART 15.247			
Low Power Mode		FCC PART 15.249			
	410 – 480 MHz	ETSI EN 300 220 category 2			
	164 – 192 MHz	ETSI EN 300 220 category 2			



1.5 Current Consumption, Static Modes

 $T_{\text{A}} = 25^{\circ}\text{C}, \, \text{VDD} = 3.0 \text{ V}, \, f_{\text{xosc}} = 32 \text{ MHz}$ if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Power Down with Retention		0.3	1	μA	
		0.5		μA	Low-power RC oscillator running
XOFF Mode		170		μA	Crystal oscillator / TCXO disabled
IDLE Mode		1.3		mA	Clock running, system waiting with no radio activity

1.6 Current Consumption, Transmit Modes

950 MHz band (High Performance Mode)

 $T_{\text{A}} = 25^{\circ}\text{C}, \, \text{VDD} = 3.0 \text{ V}, \, f_{\text{xosc}} = 32 \text{ MHz}$ if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
TX Current Consumption +10 dBm		37		mA	
TX Current Consumption 0 dBm		26		mA	

868/915/920 MHz bands (High Performance Mode)

 T_A = 25°C, VDD = 3.0 V, f_{xosc} = 40 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
TX Current Consumption +14 dBm		47		mA	
TX Current Consumption +10 dBm		38		mA	

434 MHz band (High Performance Mode)

 $T_A = 25^{\circ}C$, VDD = 3.0 V, $f_{xosc} = 40$ MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
TX Current Consumption +15 dBm		51		mA	
TX Current Consumption +14 dBm		47		mA	
TX Current Consumption +10 dBm		36		mA	

170 MHz band (High Performance Mode)

 T_A = 25°C, VDD = 3.0 V, f_{xosc} = 40 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
TX Current Consumption +15 dBm		56		mA	
TX Current Consumption +14 dBm		52		mA	
TX Current Consumption +10 dBm		40		mA	

Low Power Mode

 T_{A} = 25°C, VDD = 3.0 V, f_{c} = 869.5 MHz, f_{xosc} = 32 MHz if nothing else stated



Parameter	Min	Тур	Max	Unit	Condition
TX Current Consumption +10 dBm		32		mA	

1.7 Current Consumption, Receive Modes

High Performance Mode

 $T_{\text{A}}\,{=}\,25^{\circ}\text{C},\,\text{VDD}\,{=}\,3.0$ V, $f_{\text{c}}\,{=}\,869.5$ MHz, $f_{\text{xosc}}\,{=}\,32$ MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
RX Wait for Sync 1.2 kbps, 4 Byte Preamble		2		mA	Using RX Sniff Mode, where the receiver wakes up at regular intervals to look for an incoming
38.4kbps, 4 Byte Preamble		13.4		mA	packet
RX Peak Current, f _{xosc} = 40 MHz					Peak current consumption during
433, 868/915/920 MHz bands		26		mA	packet reception at the sensitivity
170 MHz band		27		mA	level
Average Current Consumption Check for Data Packet Every 1 Second Using Wake on Radio		15		uA	50 kbps, 5 byte preamble, 32 kHz RC oscillator used as sleep timer

Low Power Mode

 $T_{\text{A}} = 25^{\circ}\text{C}, \, \text{VDD} = 3.0 \text{ V}, \, f_{\text{c}} = 869.5 \text{ MHz}, \, f_{\text{xosc}} = 32 \text{ MHz}$ if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
RX Peak Current Low power RX mode					Peak current consumption during packet reception at the sensitivity
1.2 kbps		17		mA	level



1.8 Receive Parameters¹

General Receive Parameters (High Performance Mode)

 T_{A} = 25°C, VDD = 3.0 V, f_{c} = 869.5 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Saturation		+10		dBm	
Digital Channel Filter Programmable Bandwidth					
f _{xosc} = 32 MHz	2.8		200	kHz	
$f_{xosc} = 40 \text{ MHz}$	3.5		250	kHz	
IIP3, Normal Mode		-14		dBm	At maximum gain
IIP3, High Linearity Mode		-8		dBm	Using 6 dB gain reduction in front end
		±12		%	With carrier sense detection enabled and assuming 4 byte preamble
Datarate Offset Tolerance		±0.2		%	With carrier sense detection disabled
Spurious Emissions					Radiated emissions measured
1 - 13 GHz (VCO leakage at 3.5 GHz)		-56		dBm	according to ETSI EN 300 220, $f_c =$
30 MHz to 1 GHz		< -57		dBm	869.5 MHz
Optimum Source Impedance					
868 / 915 / 920 MHz bands 433 MHz band 169 MHz band	60 + j60 / 30+j30 100 + j60 / 50+ j30 140 + j40 / 70 + j20		Ω Ω Ω	(Differential / Single Ended RX Configurations)	

 $^{\rm 1}$ All RX measurements made at the antenna connector, to a bit error rate limit of 1%



RX performance in 950 MHz band (High Performance Mode)

 T_{A} = 25°C, VDD = 3.0 V, f_{xosc} = 32 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Sensitivity		-120		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ²
Note: Sensitivity can be improved if the TX and RX matching networks are		-107		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz
separated.		-100		dBm	200 kbps, DEV=83 kHz (outer symbols), CHF=200 kHz, 4GFSK ³
		51		dB	± 12.5 kHz (adjacent channel)
Blocking and Selectivity		52		dB	± 25 kHz (alternate channel)
1.2 kbps 2FSK, 12.5 kHz channel separation, 4 kHz deviation, 10 kHz		73		dB	± 1 MHz
channel filter		76		dB	± 2 MHz
		81		dB	± 10 MHz
Blocking and Selectivity		43		dB	± 200 kHz (adjacent channel)
50 kbps 2GFSK, 200 kHz channel		51		dB	± 400 kHz (alternate channel)
separation, 25 kHz deviation, 100 kHz channel filter		62		dB	± 1 MHz
(Same modulation format as 802.15.4g		65		dB	± 2 MHz
Mandatory Mode)		71		dB	± 10 MHz
		37		dB	± 200 kHz (adjacent channel)
Blocking and Selectivity		44		dB	± 400 kHz (alternate channel)
200 kbps 4GFSK, 83 kHz deviation (outer		55		dB	± 1 MHz
symbols), 200 kHz channel filter, zero IF		58		dB	± 2 MHz
		64		dB	± 10 MHz

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters. **CC1125**

² DEV is short for deviation, CHF is short for Channel Filter Bandwidth

³ BT=0.5 is used in all GFSK measurements



RX performance in 868/915/920 MHz bands (High Performance Mode)

 T_{A} = 25°C, VDD = 3.0 V, f_{xosc} = 32 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
		-129		dBm	300 bps, DEV=1 kHz CHF=3.8 kHz
		-129		ubiii	$f_{xosc} = 40 \text{ MHz}$
		-123		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz
		-114		dBm	4.8 kbps OOK
Sensitivity		-110		dBm	38.4 kbps, DEV=20 kHz CHF=100 kHz
		-110		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz
		-103		dBm	200 kbps, DEV=83 kHz (outer symbols), CHF=200 kHz, 4GFSK
Blocking and Selectivity		62		dB	± 6.25 kHz (adjacent channel)
0.3 kbps 2FSK, 6.25 kHz channel		63		dB	+ 12.5 kHz (alternate channel)
separation, 1 kHz deviation, 3.8 kHz channel filter		83		dB	± 1 MHz
$f_{xosc} = 40 \text{ MHz}$ using TCXO		87		dB	± 2 MHz
		91		dB	± 10 MHz
Blocking and Selectivity		58		dB	± 12.5 kHz (adjacent channel)
1.2 kbps 2FSK, 12.5 kHz channel		58		dB	± 25 kHz (alternate channel)
separation, 4 kHz deviation, 10 kHz		78		dB	± 1 MHz
channel filter		82		dB	± 2 MHz
f_{xosc} = 40 MHz using TCXO		86		dB	± 10 MHz
Blocking and Selectivity		58		dB	± 25 kHz (adjacent channel)
1.2 kbps 2FSK, 25 kHz channel		77		dB	± 1 MHz
separation, 4 kHz deviation, 16 kHz channel filter		106		dB	± 2 MHz
$f_{xosc} = 40 \text{ MHz}$ using TCXO					
Using external SAW filter for compliance with ETSI category 1		101		dB	± 10 MHz
		42		dB	+ 100 kHz (adjacent channel)
Blocking and Selectivity		43		dB	± 200 kHz (alternate channel)
38.4 kbps 2GFSK, 100 kHz channel		62		dB	± 1 MHz
separation, 20 kHz deviation, 100 kHz channel filter		66		dB	± 2 MHz
		74		dB	± 10 MHz
Blocking and Selectivity		43		dB	± 200 kHz (adjacent channel)
50 kbps 2GFSK, 200 kHz channel		50		dB	± 400 kHz (alternate channel)
separation, 25 kHz deviation, 100 kHz channel filter		61		dB	± 1 MHz
(Same modulation format as 802.15.4g		65		dB	± 2 MHz
(Same modulation format as 802.15.4g Mandatory Mode)		74		dB	± 10 MHz



Parameter	Min	Тур	Max	Unit	Condition
		36		dB	± 200 kHz (adjacent channel)
Blocking and Selectivity		44		dB	± 400 kHz (alternate channel)
200 kbps 4GFSK, 83 kHz deviation (outer		55		dB	± 1 MHz
symbols), 200 kHz channel filter, zero IF		59		dB	± 2 MHz
		67		dB	± 10 MHz
Image Rejection					
(Image compensation enabled)		58		dB	1.2 kbps, DEV=4 kHz CHF=10 kHz, image at -125 kHz
f_{xosc} = 40 MHz using TCXO					

RX performance in 434 MHz band (High Performance Mode)

 $T_{\text{A}} = 25^{\circ}\text{C}, \, \text{VDD} = 3.0 \text{ V}, \, f_{\text{xosc}} = 32 \text{ MHz}$ if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
		-129		dBm	300 bps, DEV=1 kHz CHF=3.8 kHz
		-125		dBill	$f_{xosc} = 40 \text{ MHz}$
Sensitivity		-123		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz
		-109		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz
		-116		dBm	1.2 kbps, DEV=20 kHz CHF=50 kHz
Blocking and Selectivity		65		dB	+ 6.25 kHz (adjacent channel)
0.3 kbps 2FSK, 6.25 kHz channel		66		dB	+ 12.5 kHz (alternate channel)
separation, 1 kHz deviation, 3.8 kHz channel filter		86		dB	± 1 MHz
f _{xosc} = 40 MHz using TCXO		90		dB	± 2 MHz
T _{xosc} = 40 MHZ USING TCAO		95		dB	± 10 MHz
Blocking and Selectivity		60		dB	± 12.5 kHz (adjacent channel)
1.2 kbps 2FSK, 12.5 kHz channel		61		dB	± 25 kHz (alternate channel)
separation, 4 kHz deviation, 10 kHz channel filter		80		dB	± 1 MHz
		85		dB	± 2 MHz
f_{xosc} = 40 MHz using TCXO		91		dB	± 10 MHz
		47		dB	+ 100 kHz (adjacent channel)
Blocking and Selectivity		50		dB	± 200 kHz (alternate channel)
38.4 kbps 2GFSK, 100 kHz channel separation, 20 kHz deviation, 100 kHz		67		dB	± 1 MHz
channel filter		71		dB	± 2 MHz
		78		dB	± 10 MHz



RX performance in 170 MHz band (High Performance Mode)

 T_{A} = 25°C, VDD = 3.0 V, f_{xosc} = 32 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Sensitivity		-129		dBm	300 bps, DEV=1 kHz CHF=3.8 kHz f _{xosc} = 40 MHz
		-123		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz
Blocking and Selectivity		67		dB	± 6.25 kHz (adjacent channel)
0.3 kbps 2FSK, 6.25 kHz channel		67		dB	+ 12.5 kHz (alternate channel)
separation, 1 kHz deviation, 3.8 kHz channel filter		88		dB	± 1 MHz
$f_{xosc} = 40 \text{ MHz using TCXO}$		101		dB	- 2 MHz
$T_{xosc} = 40$ WHZ USING TCAO		104		dB	± 10 MHz
Blocking and Selectivity		63		dB	± 12.5 kHz (adjacent channel)
1.2 kbps 2FSK, 12.5 kHz channel		65		dB	± 25 kHz (alternate channel)
separation, 4 kHz deviation, 10 kHz channel filter		82		dB	± 1 MHz
$f_{xosc} = 40 \text{ MHz using TCXO}$		86		dB	± 2 MHz
		93		dB	- 10 MHz
Spurious Response Rejection					
1.2 kbps 2FSK, 12.5 kHz channel separation, 4 kHz deviation, 10 kHz channel filter		70		dB	
Image Rejection (Image compensation enabled)		66		dB	1.2 kbps, DEV=4 kHz CHF=10 kHz, image at -125 kHz





RX performance in Low Power Mode

 T_{A} = 25°C, VDD = 3.0 V, f_{c} = 869.5 MHz, f_{xosc} = 32 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
		-111		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz
Sensitivity		-99		dBm	38.4 kbps, DEV=50 kHz CHF=100 kHz
		-99		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz
		46		dB	± 12.5 kHz (adjacent channel)
Blocking and Selectivity		46		dB	± 25 kHz (alternate channel)
1.2 kbps 2FSK, 12.5 kHz channel separation, 4 kHz deviation, 10 kHz		73		dB	± 1 MHz
channel filter		78		dB	± 2 MHz
		79		dB	± 10 MHz
		43		dB	± 50 kHz (adjacent channel)
Blocking and Selectivity		45		dB	+ 100 kHz (alternate channel)
1.2 kbps 2FSK, 50 kHz channel separation, 20 kHz deviation, 50 kHz		71		dB	± 1 MHz
channel filter		74		dB	± 2 MHz
		75		dB	± 10 MHz
Blocking and Selectivity		37		dB	+ 100 kHz (adjacent channel)
38.4 kbps 2GFSK, 100 kHz channel		43		dB	+ 200 kHz (alternate channel)
separation, 20 kHz deviation, 100 kHz		58		dB	± 1 MHz
channel filter		62		dB	± 2 MHz
		64		dB	+ 10 MHz
Blocking and Selectivity		43	1	dB	+ 200 kHz (adjacent channel)
50 kbps 2GFSK, 200 kHz channel		52	1	dB	+ 400 kHz (alternate channel)
separation, 25 kHz deviation, 100 kHz channel filter		60	1	dB	± 1 MHz
(Same modulation format as 802.15.4g		64	1	dB	± 2 MHz
Mandatory Mode)		65	1	dB	± 10 MHz
Saturation		+10	1	dBm	



1.9 Transmit Parameters

 T_{A} = 25°C, VDD = 3.0 V, f_{c} = 869.5 MHz, f_{xosc} = 32 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
		+12		dBm	At 950 MHz
		+14		dBm	At 915/920 MHz
		+15		dBm	At 915/920 MHz with VDD = 3.6 V
		+15		dBm	At 868 MHz
Max Output Power		+16		dBm	At 868 MHz with VDD = 3.6 V
		+15		dBm	At 433 MHz
		+16		dBm	At 433 MHz with VDD = 3.6 V
		+15		dBm	At 170 MHz
		+16		dBm	At 170 MHz with VDD = 3.6 V
Min Output Power		-11		dBm	Within fine step size range
		-40		dBm	Within coarse step size range
Output Power Step Size		0.4		dB	Within fine step size range
Adjacent Channel Power		-75		dBc	4-GFSK 9.6 kbps in 12.5 kHz channel, measured in 100 Hz bandwidth at 434 MHz (FCC Part 90 Mask D compliant)
		-58		dBc	4-GFSK 9.6 kbps in 12.5 kHz channel, measured in 8.75 kHz bandwidth (ETSI 300 220 compliant)
		-61		dBc	2-GFSK 2.4 kbps in 12.5 kHz channel, 1.2 kHz deviation
Spurious Emissions (Not including harmonics)		< -60		dBm	
Harmonics 2nd Harm, 170 MHz 3rd Harm, 170 MHz 2nd Harm, 470 MHz 2nd Harm, 433 MHz 2nd Harm, 433 MHz 2nd Harm, 450 MHz 3rd Harm, 450 MHz 2nd Harm, 868 MHz 2nd Harm, 868 MHz 2nd Harm, 915 MHz 3rd Harm, 915 MHz 4 th Harm, 915 MHz 2nd Harm, 950 MHz 3rd Harm, 950 MHz		-39 -58 -56 -51 -60 -45 -40 -42 56 52 60 -58 -42		dBm dBm dBm dBm dBm dBm dBm dBuV/m dBuV/m dBuV/m dBm dBm	Transmission at +14 dBm (or maximum allowed in applicable band where this is less than +14 dBm) using TI reference design Emissions measured according to ARIB T-96 in 950 MHz band, ETSI EN 300-220 in 170, 433 and 868 MHz bands and FCC part 15.247 in 450 and 915 MHz band Fourth harmonic in 915 MHz band will require extra filtering to meet FCC requirements if transmitting for long intervals (>50 ms periods)
Optimum Load Impedance 868 / 915 / 920 MHz bands 433 MHz band 169 MHz band		35 + j35 55 + j25 80 + j0		Ω Ω Ω	



1.10 PLL Parameters

High Performance Mode

 T_{A} = 25°C, VDD = 3.0 V, f_{c} = 869.5 MHz, f_{xosc} = 40 MHz using TCXO if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Phase Noise in 950 MHz Band		-100		dBc/Hz	± 10 kHz offset
$f_{\text{xosc}} = 32 \text{ MHz}$		-103		dBc/Hz	± 100 kHz offset
		-123		dBc/Hz	± 1 MHz offset
		-101		dBc/Hz	± 10 kHz offset
Phase Noise in 868/915/920 MHz Bands		-102		dBc/Hz	± 100 kHz offset
		-124		dBc/Hz	± 1 MHz offset
		-107		dBc/Hz	± 10 kHz offset
Phase Noise in 433 MHz Band		-110		dBc/Hz	± 100 kHz offset
		-130		dBc/Hz	± 1 MHz offset
Phase Noise in 170 MHz Band		-115		dBc/Hz	± 10 kHz offset
		-115		dBc/Hz	± 100 kHz offset
		-135		dBc/Hz	± 1 MHz offset

Low Power Mode

 $T_{\text{A}} = 25^{\circ}\text{C}, \, \text{VDD} = 3.0 \text{ V}, \, f_{\text{c}} = 869.5 \text{ MHz}, \, f_{\text{xosc}} = 32 \text{ MHz}$ if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
		-90		dBc/Hz	± 10 kHz offset
Phase Noise in 950 MHz Band		-92		dBc/Hz	± 100 kHz offset
		-124		dBc/Hz	± 1 MHz offset
		-95		dBc/Hz	± 10 kHz offset
Phase Noise in 868/915/920 MHz Bands		-95		dBc/Hz	± 100 kHz offset
		-124		dBc/Hz	± 1 MHz offset
		-98		dBc/Hz	± 10 kHz offset
Phase Noise in 433 MHz Band		-102		dBc/Hz	± 100 kHz offset
		-129		dBc/Hz	± 1 MHz offset
		-106		dBc/Hz	± 10 kHz offset
Phase Noise in 170 MHz Band		-110		dBc/Hz	± 100 kHz offset
		-136		dBc/Hz	± 1 MHz offset





1.11 Wake-up and Timing

 $T_{\text{A}} = 25^{\circ}\text{C}, \, \text{VDD} = 3.0 \text{ V}, \, f_{\text{c}} = 869.5 \text{ MHz}, \, f_{\text{xosc}} = 32 \text{ MHz}$ if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Powerdown to IDLE		0.4		ms	Depends on crystal
IDLE to RX/TX		166		μs	Calibration disabled
		461		μs	Calibration enabled
RX/TX Turnaround		50		μs	
RX/TX to IDLE time		296		μs	Calibrate when leaving RX/TX enabled
		0		μs	Calibrate when leaving RX/TX disabled
Frequency Synthesizer Calibration		0.4		ms	When using SCAL strobe
Minimum Required Number of Preamble Bytes		0.5		bytes	Required for RF front end gain settling only. Digital demodulation does not require preamble for settling
Time From Start RX Until Valid RSSI		4.6		ms	12.5 kHz channels
Including gain settling (function of channel bandwidth. Programmable for trade-off between speed and accuracy)		0.3		ms	200 kHz channels

1.12 High Speed Crystal Oscillator

 T_{A} = 25°C, VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Мах	Unit	Condition		
Crystal Frequency	32		44	MHz	Note: It is recommended that the crystal frequency is chosen so that the RF channel(s) are >1 MHz away from multiples of XOSC in TX and XOSC/2 in RX		
Load Capacitance (C _L)		10		pF			
ESR		<50		Ω			
Start-up Time		0.4		ms	Depends on crystal		

1.13 High Speed Clock Input (TCXO)

 $T_A = 25^{\circ}C$, VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Clock Frequency	32		44	MHz	
Clock input amplitude (peak-to-peak)		>0.8		V	Should not exceed supply voltage



1.14 32 kHz Clock Input

 $T_A = 25^{\circ}C$, VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Clock Frequency		32		kHz	
32 kHz Clock Input Pin Input High Voltage	0.8×VDD			V	
32 kHz Clock Input Pin Input Low Voltage			0.2×VDD	V	

1.15 Low Speed RC Oscillator

 $T_A = 25^{\circ}C$, VDD = 3.0 V if nothing else stated.

Parameter	Min	Тур	Мах	Unit	Condition
Frequency		32/40		kHz	After Calibration (calibrated against the high speed XOSC)
Frequency Accuracy After Calibration		±0.1		%	Relative to frequency reference (i.e. 32 MHz crystal or TCXO)
Initial Calibration Time		1.6		ms	

1.16 I/O and Reset

 $T_A = 25^{\circ}C$, VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Logic Input High Voltage	0.8×VDD			V	
Logic Input Low Voltage			0.2×VDD	V	
Logic Output High Voltage	0.8×VDD			V	At 4 mA output load or less
Logic Output Low Voltage			0.2×VDD	V	At 4 mA output load of less
Power-on Reset Threshold		1.3		V	Voltage on DVDD pin

1.17 Temperature Sensor

 $T_A = 25^{\circ}C$, VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Temperature Sensor Range	-40		85	°C	
Temperature Coefficient		2.66		mV / °C	Change in sensor output voltage vs change in temperature
Typical Output Voltage		794		mV	Typical sensor output voltage at $T_A = 25^{\circ}C$, VDD = 3.0 V
VDD Coefficient		1.17		mV / V	Change in sensor output voltage vs change in VDD

The **CC1125** can be configured to provide a voltage proportional to temperature on GPIO1. Using the information above, the temperature can be estimated by measuring this voltage. Please refer to the **CC1125** user guide for more information.



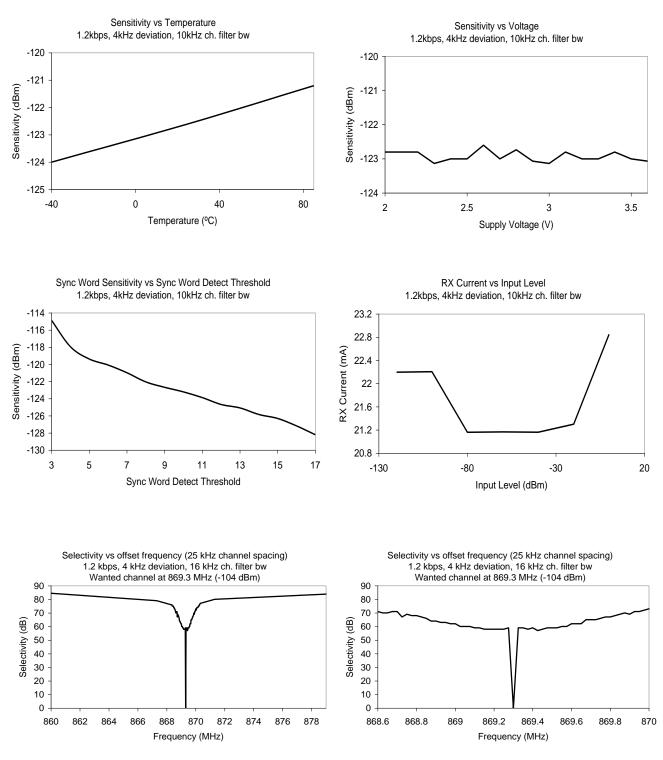
CC1125

2 Typical Performance Curves

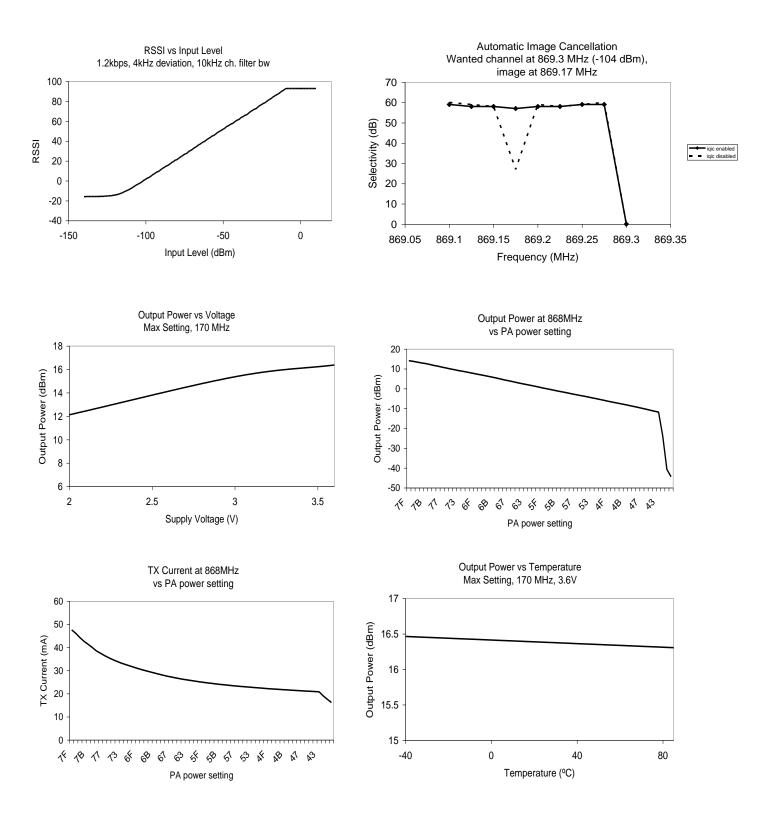
 T_{A} = 25°C, VDD = 3.0 V, f_{c} = 869.5 MHz if nothing else stated

All measurements performed on CC1120EM_868_915 rev.1.0.1, CC1120EM_955 rev.1.2.1, CC1120EM_420_470 rev.1.0.1 or CC1120EM_169 rev.1.2 ($f_{xosc} = 32$ MHz), and CC1125EM_868_915 rev.1.1.0, CC1125EM_420_470 rev.1.1.0, CC1125EM_169 rev.1.1.0, CC1125EM-Cat1-868 ($f_{xosc} = 40$ MHz)

Note that the "output power vs load impedance" plot was measured at the 50 Ω antenna connector



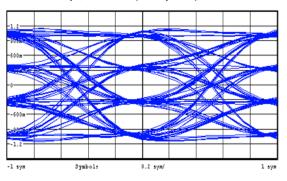




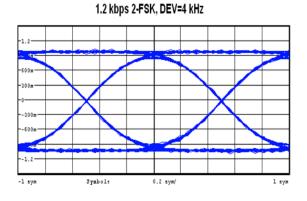


Eye Diagram

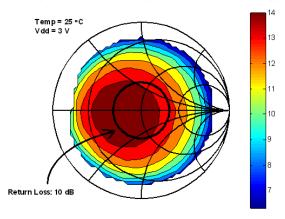
200 kbps, DEV=83 kHz (outer symbols), 4GFSK

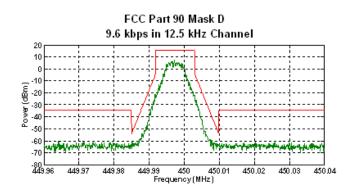


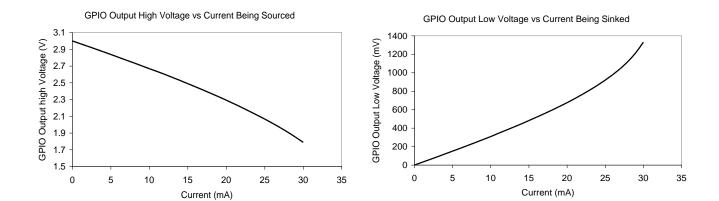
Eye Diagram



Output Power vs Load impedance (+14dBm setting)









3 Pin Configuration

The **CC1125** pin-out is shown in the table below.

Pin #	Pin name	Type / direction	Description
1	VDD_GUARD	Power	2.0 - 3.6 V VDD
2	RESET_N	Digital Input	Asynchronous, active-low digital reset
3	GPIO3	Digital Input/Output	General purpose IO
4	GPIO2	Digital Input/Output	General purpose IO
5	DVDD	Power	2.0 - 3.6 VDD to internal digital regulator
6	DCPL	Power	Digital regulator output to external decoupling capacitor
7	SI	Digital Input	Serial data in
8	SCLK	Digital Input	Serial data clock
9	SO(GPIO1)	Digital Input/Output	Serial data out (General purpose IO)
10	GPIO0	Digital Input/Output	General purpose IO
11	CSn	Digital Input	Active-low chip-select
12	DVDD	Power	2.0 - 3.6 V VDD
13	AVDD_IF	Power	2.0 - 3.6 V VDD
14	RBIAS	Analog	External high precision R
15	AVDD_RF	Power	2.0 - 3.6 V VDD
16	N.C.		Not Connected
17	PA	Analog	Single-ended TX output
18	TRX_SW	Analog	TX/RX switch
19	LNA_P	Analog	Differential RX input
20	LNA_N	Analog	Differential RX input
21	DCPL_VCO	Power	Pin for external decoupling of VCO supply regulator
22	AVDD_SYNTH1	Power	2.0 - 3.6 V VDD
23	LPF0	Analog	External loopfilter components
24	LPF1	Analog	External loopfilter components
25	AVDD_PFD_CHP	Power	2.0 - 3.6 V VDD
26	DCPL_PFD_CHP	Power	Pin for external decoupling of PFD and CHP regulator
27	AVDD_SYNTH2	Power	2.0 - 3.6 V VDD
28	AVDD_XOSC	Power	2.0 - 3.6 V VDD
29	DCPL_XOSC	Power	Pin for external decoupling of XOSC supply regulator
30	XOSC_Q1	Analog	Crystal oscillator pin 1 (must be grounded if a TCXO or other external clock connected to EXT_XOSC is used)
31	XOSC_Q2	Analog	Crystal oscillator pin 2 (must be left floating if a TCXO or other external clock connected to EXT_XOSC is used)
32	EXT_XOSC	Digital Input	Pin for external XOSC input (must be grounded if a regular XOSC connected to XOSC_Q1 and XOSC_Q2 is used)
-	GND	Ground Pad	The ground pad must be connected to a solid ground plane



4 Block Diagram

A system block diagram of **CC1125** is shown Figure 4.1.

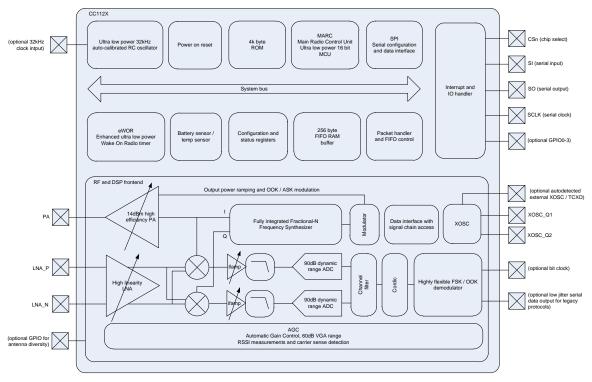


Figure 4.1 : System Block Diagram

4.1 Frequency Synthesizer

At the heart of **CC1125** there is a fully integrated, fractional-N, ultra high performance frequency synthesizer. The frequency synthesizer is designed for excellent phase noise performance, providing very high selectivity and blocking performance. The system is designed to comply with the most stringent regulatory spectral masks at maximum transmit power.

Either a crystal can be connected to XOSC_Q1 and XOSC_Q2, or a TCXO can be connected to the EXT_XOSC input. The oscillator generates the reference frequency for the synthesizer, as well as clocks for the ADC and the digital part. To reduce system cost, **CC1125** has high accuracy frequency estimation and compensation registers to measure and compensate for crystal inaccuracies, enabling the use of lower cost crystals. If a TCXO is used, the **CC1125** will automatically turn the TCXO on and off when needed to support low power modes and Wake-On-Radio operation.

4.2 Receiver

CC1125 features a highly flexible receiver. The received RF signal is amplified by the low-noise amplifier (LNA) and down-converted in quadrature (I and Q) to the intermediate frequency (IF). At IF, the I/Q signals are digitized by the high dynamic range ADCs.

An advanced Automatic Gain Control (AGC) unit adjusts the front end gain, and enables the **CC1125** to receive both strong and weak signals, even in the presence of strong interferers. High attenuation channel and data filtering enable reception with strong neighbor channel interferers. The I/Q signal is converted to a phase / magnitude signal to support both FSK and OOK modulation schemes.

A sophisticated pattern recognition algorithm locks onto the synchronization word without need for preamble settling bytes. Receiver settling time is therefore reduced to the settling time of the



AGC, typically 4 bits. The advanced pattern recognition also greatly reduces the problem of false sync triggering on noise, further reducing power consumption and improving sensitivity and reliability. The pattern recognition logic can also be used as a high performance preamble detector to reliably detect a valid preamble in the channel.

A novel I/Q compensation algorithm removes any problem of I/Q mismatch and hence avoids time consuming and costly I/Q / image calibration steps in production or in the field.

4.3 Transmitter

The **CC1125** transmitter is based on direct synthesis of the RF frequency (in-loop modulation). To achieve effective spectrum usage, **CC1125** has extensive data filtering and shaping in TX to support high throughput data communication in narrowband channels. The modulator also controls power ramping to remove issues such as spectral splattering when driving external high power RF amplifiers.

4.4 Radio Control and User Interface

The **CC1125** digital control system is built around MARC (Main Radio Control) implemented using an internal high performance 16 bit ultra low power processor. MARC handles power modes, radio sequencing and protocol timing.

A 4-wire SPI serial interface is used for configuration and data buffer access. The digital baseband includes support for channel configuration, packet handling, and data buffering. The host MCU can stay in power down until a valid RF packet has been received, and then burst read the data, greatly reducing the power consumption and computing power required from the host MCU.

The **CC1125** radio control and user interface is based on the widely used **CC1101** transceiver to enable easy SW transition between the two platforms. The command strobes and the main radio states are the same for the two platforms.

For legacy formats **CC1125** also has support for two serial modes. In synchronous serial mode **CC1125** performs bit synchronization and provides the MCU with a bit clock with associated data. In transparent mode **CC1125** outputs the digital baseband signal using a digital interpolation filter to eliminate jitter introduced by digital filtering and demodulation.

4.5 Enhanced Wake-On-Radio (eWOR)

eWOR, using a flexible integrated sleep timer, enables automatic receiver polling with no intervention from the MCU. The **CC1125** will enter RX, listen and return to sleep if a valid RF packet is not received. The sleep interval and duty cycle can be configured to make a trade-off between network latency and power consumption. Incoming messages are time-stamped to simplify timer re-synchronization.

The eWOR timer runs off an ultra low power 32 kHz RC oscillator. To improve timing accuracy, the RC oscillator can be automatically calibrated to the RF crystal in configurable intervals.

4.6 Sniff Mode

The **CC1125** supports very quick start up times, and requires very few preamble bits. Sniff Mode uses this to dramatically reduce the current consumption while the receiver is waiting for data.

Since the **CC1125** is able to wake up and settle much faster than the length of most preambles, it is not required to be in RX continuously while waiting for a packet to arrive. Instead, the enhanced wake-on-radio feature can be used to put the device into sleep periodically. By setting an appropriate sleep time, the **CC1125** will be able to wake up and receive the packet when it arrives with no performance loss. This removes the need for accurate timing synchronization between transmitter and receiver, and allows the user to trade off current consumption between the transmitter and receiver.



CC1125

4.7 Antenna Diversity

Antenna diversity can increase performance in a multi-path environment. An external antenna switch is required. The switch can be automatically controlled by **CC1125** using one of the GPIO pins (also support for differential output control signal typically used in RF switches).

If antenna diversity is enabled, the GPIO will alternate between states until a valid RF input signal is detected. An optional acknowledge packet can be transmitted without changing GPIO state.

An incoming RF signal can be validated by received signal strength, by using the automatic preamble detector, or a combination of the two. Using the preamble detector will make a more robust system and avoid the need to set a defined signal strength threshold, as this threshold will set the sensitivity limit of the system.



CC1125

5 Typical Application Circuit

Very few external components are required for the operation of **CC1125**. A typical application circuit is shown below. Note that it does not show how the board layout should be done, which will greatly influence the RF performance of **CC1125**.

This section is meant as an introduction only. Note that decoupling capacitors for power pins are not shown in the figure below.

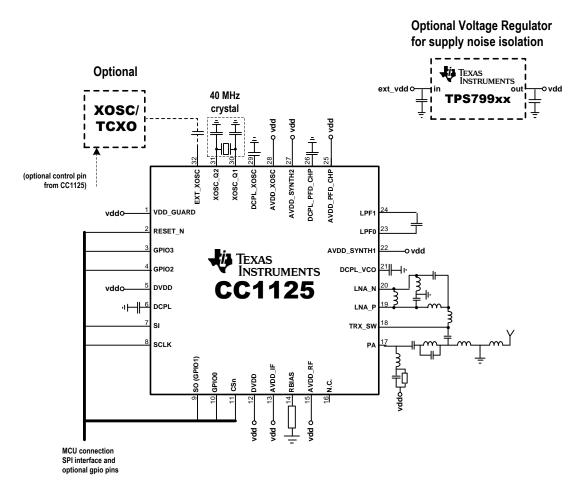


Figure 5.1 : Typical Application Circuit



6 History

Revision	Date	Description / Changes
SWRS120B	March 2013	Added ARIB T-108 to list of regulations
		Added ETSI EN 301 166 to list of regulations
		Added optimum source / load impedance
		Added missing unit "dBm" in output power section
		Added temperature sensor data
		Clarified how the typical performance curves have been measured
		Corrected wrong deviation for 38.4 kbps sensitivity (was 50 kHz, corrected to 20 kHz)
		Pin CS_N renamed to CSn to comply with naming convention used in the user guide
		Updated typical frequency of low frequency RCOSC to show that it scales with the reference it is calibrated against (i.e. the high speed XOSC)
		Updated modulation format information in image rejection sections
		Stated which ETSI EN 300 220 receiver category that is suitable for low power mode
		Clarified under max ratings that I/O voltages should not exceed device supply voltage by more than 0.3 V $$
		Various minor spelling errors corrected
SWRS120	March 2012	Initial release

CC1125



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	•	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
CC1125RHBR	ACTIVE	VQFN	RHB	32	3000	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-3-260C-168 HR	-40 to 85	CC1125	Samples
CC1125RHBT	ACTIVE	VQFN	RHB	32	250	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-3-260C-168 HR	-40 to 85	CC1125	Samples
CC1125RHMR	NRND	VQFN	RHM	32	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 85	CC1125	
CC1125RHMT	NRND	VQFN	RHM	32	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 85	CC1125	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CC1125RHBR	VQFN	RHB	32	3000	330.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2
CC1125RHBT	VQFN	RHB	32	250	180.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CC1125RHBR	VQFN	RHB	32	3000	338.1	338.1	20.6
CC1125RHBT	VQFN	RHB	32	250	210.0	185.0	35.0



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) Package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO-220.



RHB (S-PVQFN-N32)

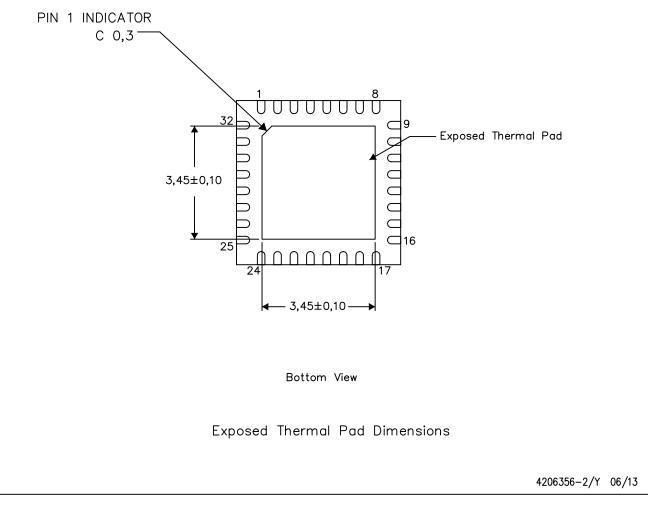
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

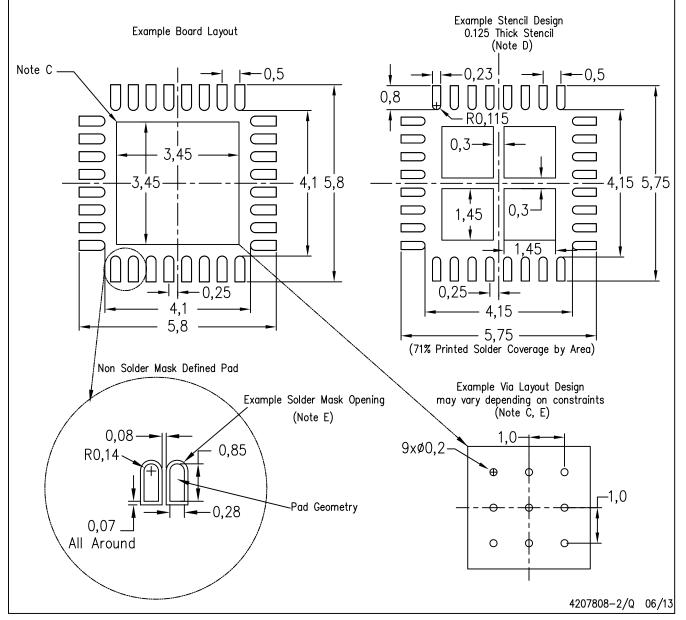


NOTE: A. All linear dimensions are in millimeters



RHB (S-PVQFN-N32)

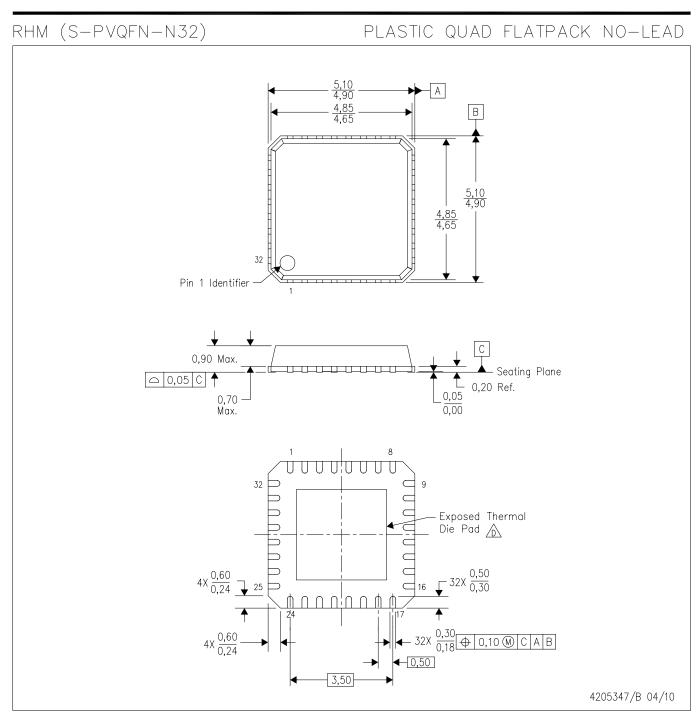
PLASTIC QUAD FLATPACK NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- E. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.







A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) Package configuration.

The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.



THERMAL PAD MECHANICAL DATA

RHM (S-PVQFN-N32)

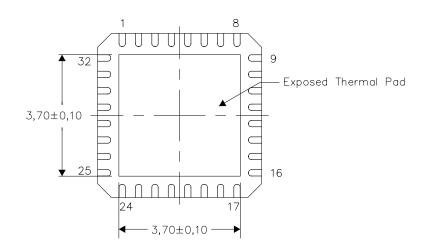
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.





NOTE: All linear dimensions are in millimeters

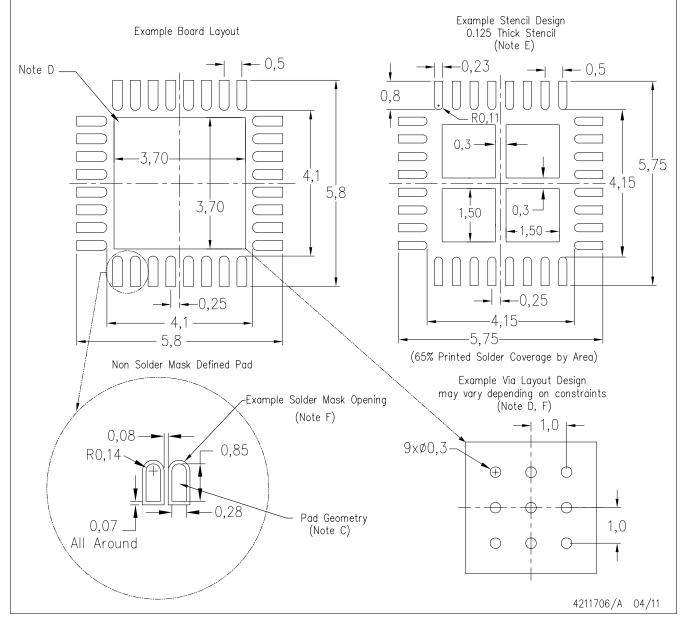
Exposed Thermal Pad Dimensions



4210977-3/A 06/10

RHM (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.



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